

# FDD5N50F

## N-Channel MOSFET, FRFET

### 500V, 3.5A, 1.55Ω

#### Features

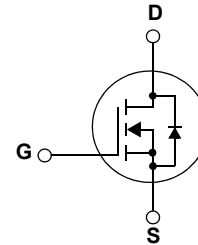
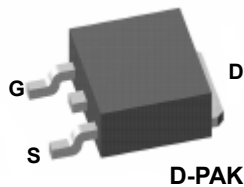
- $R_{DS(on)} = 1.25\Omega$  (Typ.) @  $V_{GS} = 10V, I_D = 1.75A$
- Low gate charge (Typ. 11nC)
- Low  $C_{RSS}$  (Typ. 5pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant



#### Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pluse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor-correction.



#### MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted\*

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain to Source Voltage	500	V
$V_{GSS}$	Gate to Source Voltage	$\pm 30$	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ C$ )	3.5
		- Continuous ( $T_C = 100^\circ C$ )	2.1
$I_{DM}$	Drain Current	- Pulsed (Note 1)	14
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	257
$I_{AR}$	Avalanche Current	(Note 1)	3.5
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	4
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5
$P_D$	Power Dissipation	( $T_C = 25^\circ C$ )	40
		- Derate above $25^\circ C$	0.3
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ C$

#### Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.4	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	110	

**Package Marking and Ordering Information**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD5N50F	FDD5N50FTM	D-PAK	380mm	16mm	2500
FDD5N50F	FDD5N50FTF	D-PAK	380mm	16mm	2000

**Electrical Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$	500	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.6	-	$V/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}, V_{GS} = 0\text{V}$ $V_{DS} = 400\text{V}, T_C = 125^\circ\text{C}$	-	-	10 100	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	-	-	$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 1.75\text{A}$	-	1.25	1.55	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{V}, I_D = 1.75\text{A}$ (Note 4)	-	4.3	-	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	490	650	pF
$C_{oss}$	Output Capacitance		-	66	88	pF
$C_{rss}$	Reverse Transfer Capacitance		-	5	7.5	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 400\text{V}, I_D = 5\text{A}$ $V_{GS} = 10\text{V}$	-	11	15	nC
$Q_{gs}$	Gate to Source Gate Charge		-	3	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	5	-	nC

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{V}, I_D = 5\text{A}$ $R_G = 25\Omega$	-	13	36	ns
$t_r$	Turn-On Rise Time		-	22	54	ns
$t_{d(off)}$	Turn-Off Delay Time		-	28	66	ns
$t_f$	Turn-Off Fall Time		-	20	50	ns

**Drain-Source Diode Characteristics**

$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	3.5	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	14	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_{SD} = 3.5\text{A}$	-	-	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{V}, I_{SD} = 5\text{A}$	-	65	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100\text{A}/\mu\text{s}$ (Note 4)	-	0.120	-	$\mu\text{C}$

**Notes:**

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2:  $L = 42\text{mH}, I_{AS} = 3.5\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
- 3:  $I_{SD} \leq 3.5\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
- 4: Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$
- 5: Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

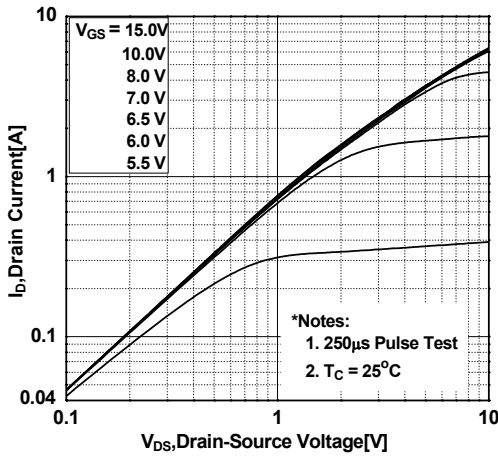


Figure 2. Transfer Characteristics

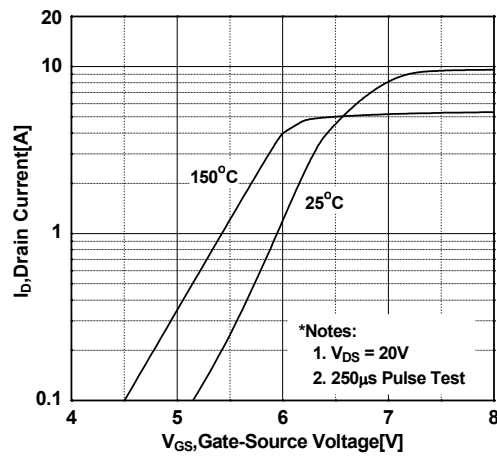


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

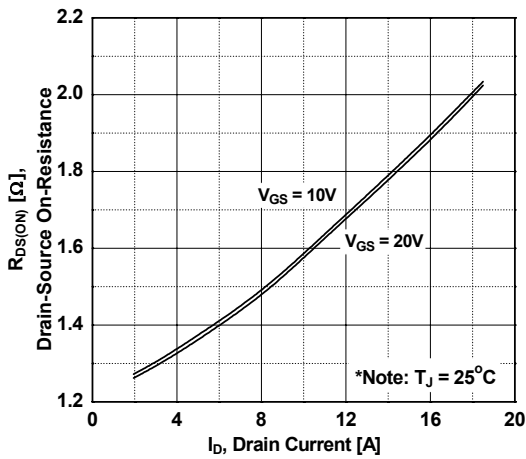


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

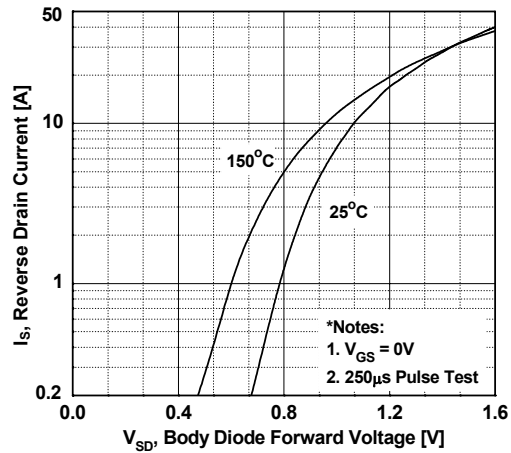


Figure 5. Capacitance Characteristics

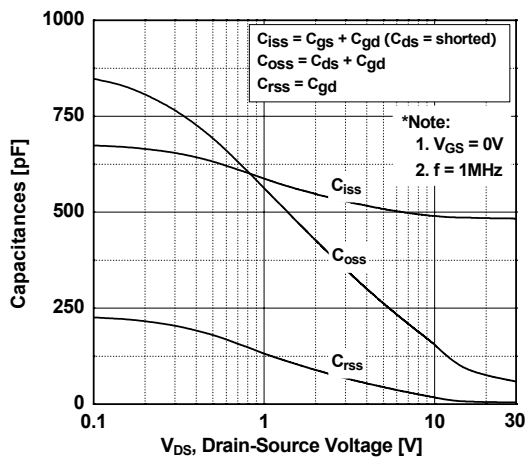
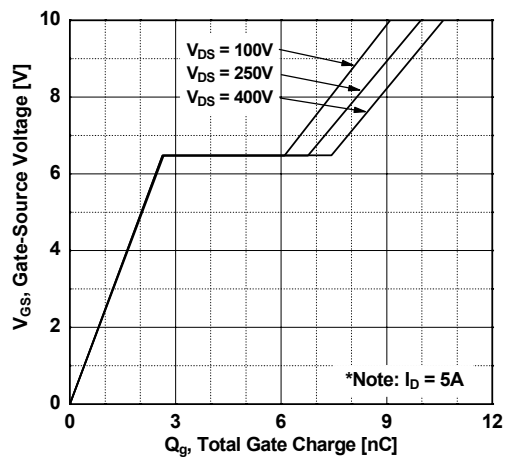
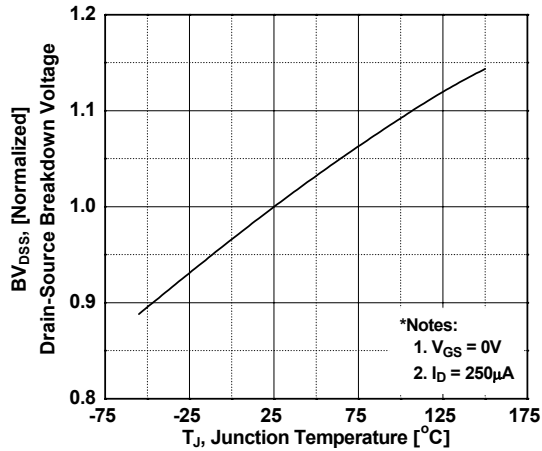


Figure 6. Gate Charge Characteristics

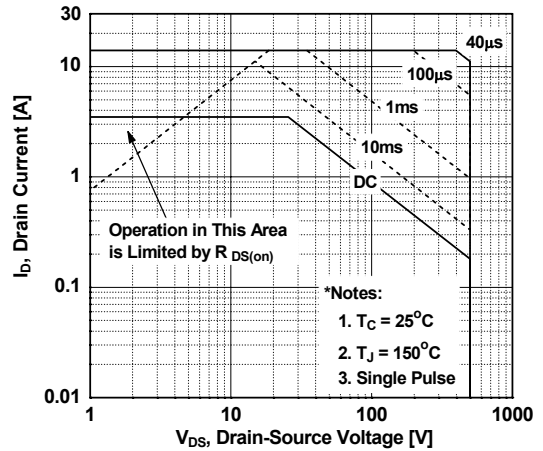


**Typical Performance Characteristics** (Continued)

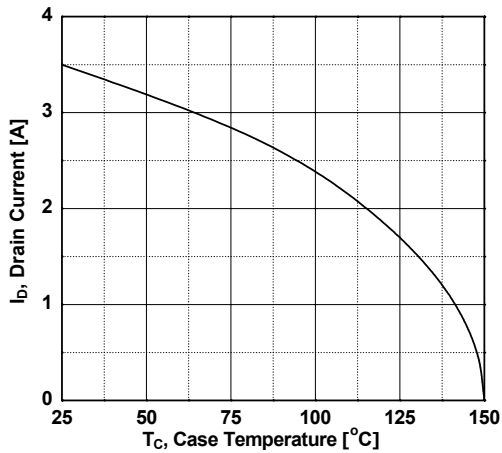
**Figure 7. Breakdown Voltage Variation vs. Temperature**



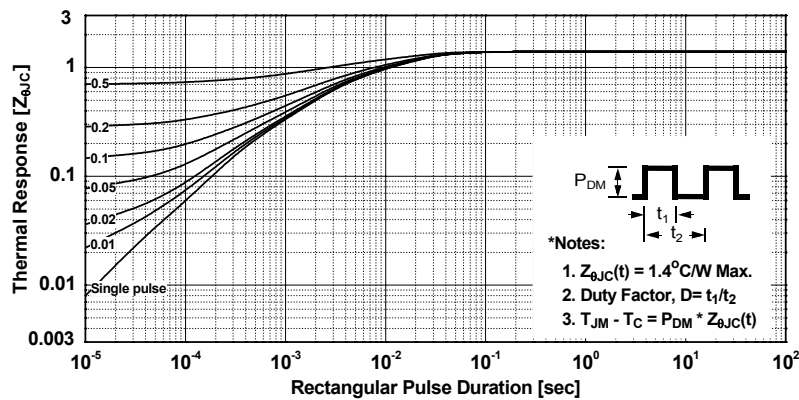
**Figure 8. Maximum Safe Operating Area**



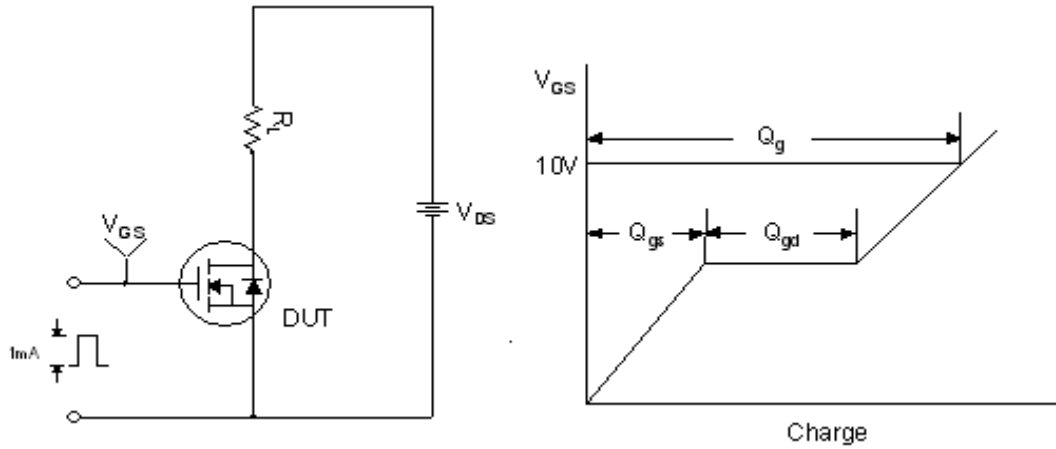
**Figure 9. Maximum Drain Current**



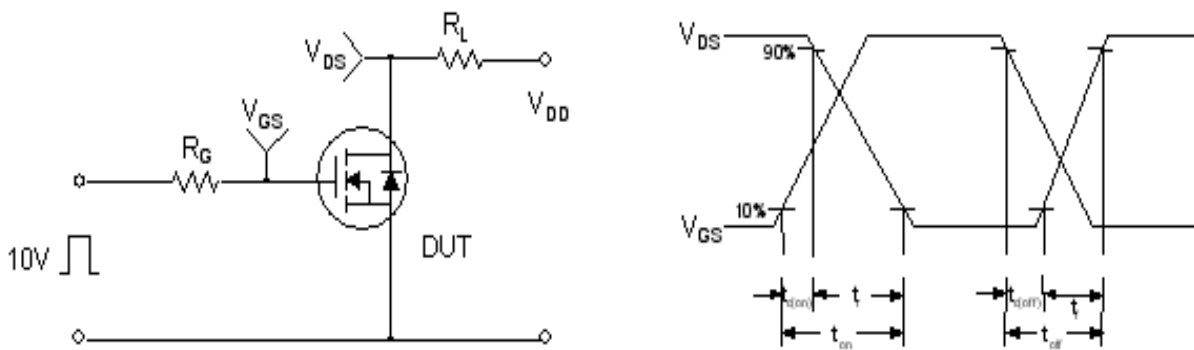
**Figure 10. Transient Thermal Response Curve**



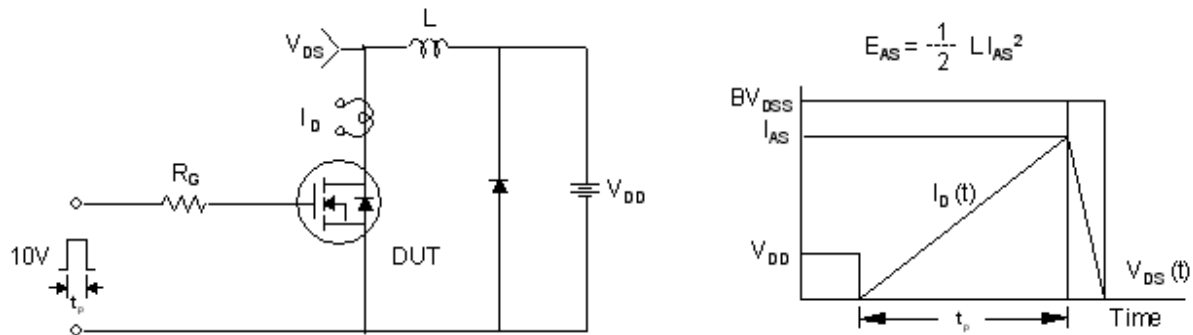
**Gate Charge Test Circuit & Waveform**



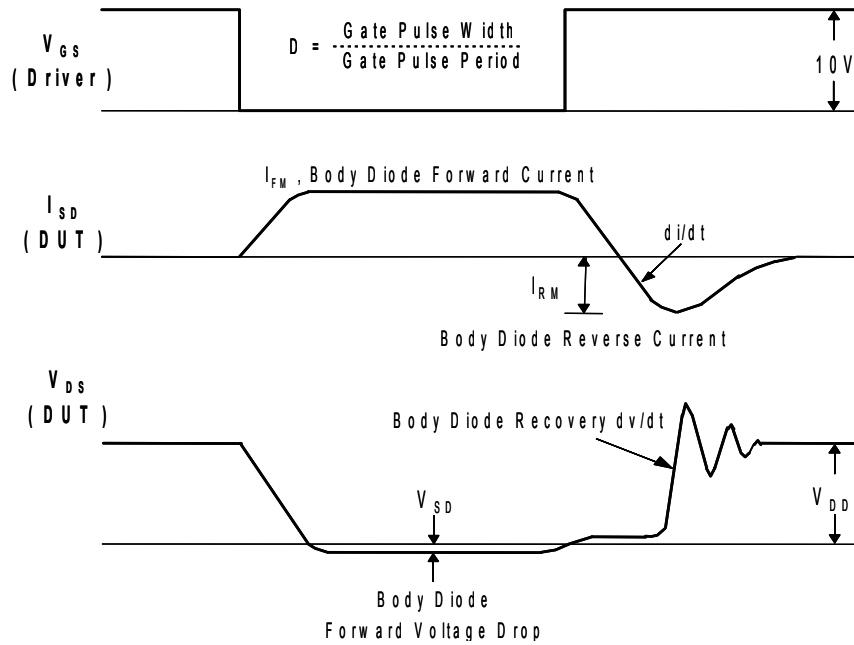
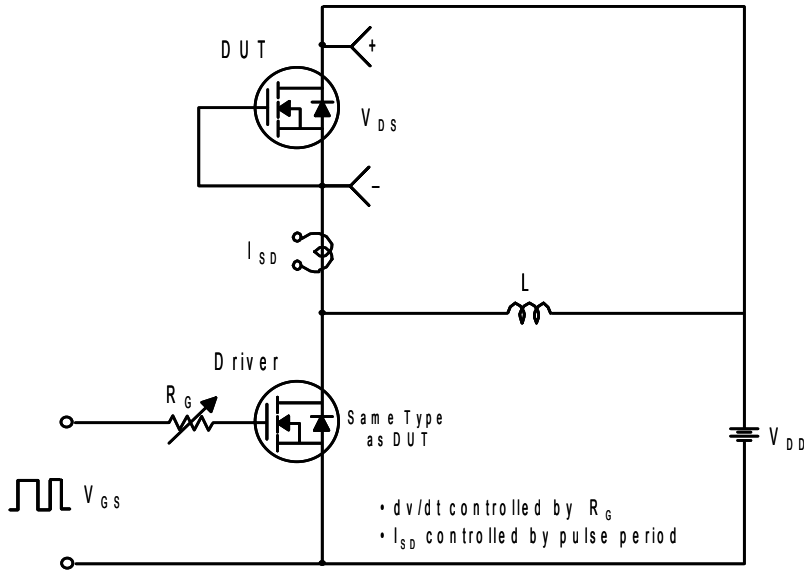
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

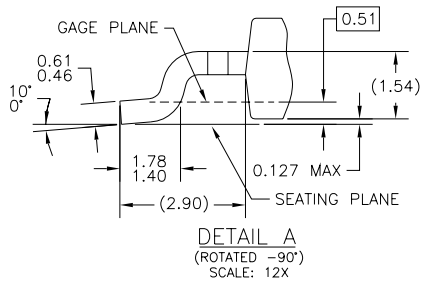
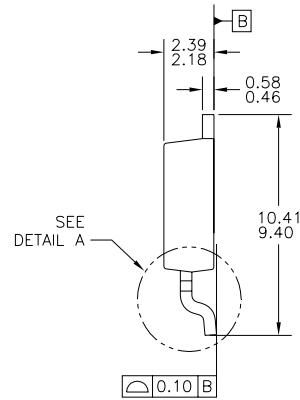
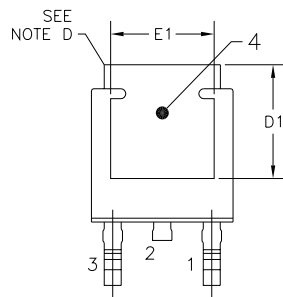
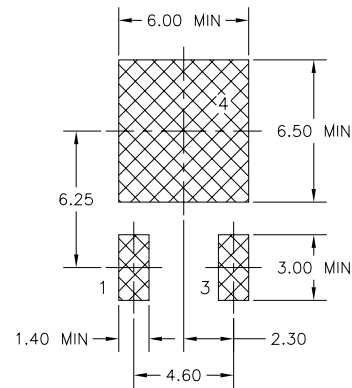
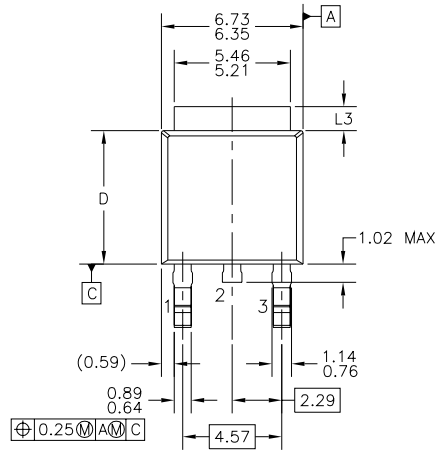


Peak Diode Recovery dv/dt Test Circuit & Waveforms



## Mechanical Dimensions

### D-PAK



- NOTES: UNLESS OTHERWISE SPECIFIED
- ALL DIMENSIONS ARE IN MILLIMETERS.
  - THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA & AB, DATED NOV. 1999.
  - DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
  - HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
  - DIMENSIONS L3,D,E1&D1 TABLE:
 





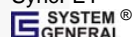
	OPTION AA	OPTION AB
L3	0.89-1.27	1.52-2.03
D	5.97-6.22	5.33-5.59
E1	4.32 MIN	3.81 MIN
D1	5.21 MIN	4.57 MIN
  - PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.

Dimensions in Millimeters



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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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